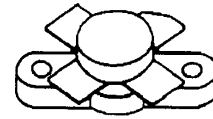


# MS1076

## RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

### Features

- 30 MHz
- 28 VOLTS
- GOLD METALLIZATION
- $P_{OUT} = 220$  W PEP
- $G_P = 12$  dB GAIN MINIMUM
- COMMON EMITTER CONFIGURATION

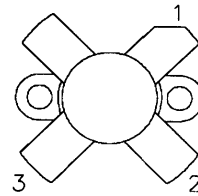


.500 4LFL (M174)  
epoxy sealed

### DESCRIPTION

The MS1076 is a 28 volt epitaxial NPN silicon planar transistor designed primarily for SSB and VHF communications. This device utilizes an emitter ballasted die geometry for maximum ruggedness and reliability.

#### PIN CONNECTION



1. Collector      3. Base  
2. Emitter      4. Emitter

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$ )

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector - Base Voltage	70	V
$V_{CEO}$	Collector - Emitter Voltage	35	V
$V_{EBO}$	Emitter - Base Voltage	4.0	V
$I_C$	Device Current	16	A
$P_{DISS}$	Power Dissipation	250	W
$T_J$	Junction Temperature	+200	$^{\circ}C$
$T_{STG}$	Storage Temperature	- 65 to +150	$^{\circ}C$

### Thermal Data

$R_{TH(J-C)}$	Junction - Case Thermal Resistance	0.7	$^{\circ}C/W$
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Rev A: October 2009

**ELECTRICAL SPECIFICATIONS (Tcase = 25°C)**
**STATIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
$BV_{CES}$	$I_C = 100 \text{ mA}$	70	---	---	V
$BV_{CEO}$	$I_C = 200 \text{ mA}$	35	---	---	V
$BV_{EBO}$	$I_E = 20 \text{ mA}$	4.0	---	---	V
$I_{CEO}$	$V_{CE} = 30 \text{ V}$	---	---	5	mA
$I_{CES}$	$V_{CE} = 35 \text{ V}$	---	---	5	mA
$H_{FE}$	$V_{CE} = 5 \text{ V},$ $I_C = 7 \text{ A}$	15	---	60	---

**DYNAMIC**

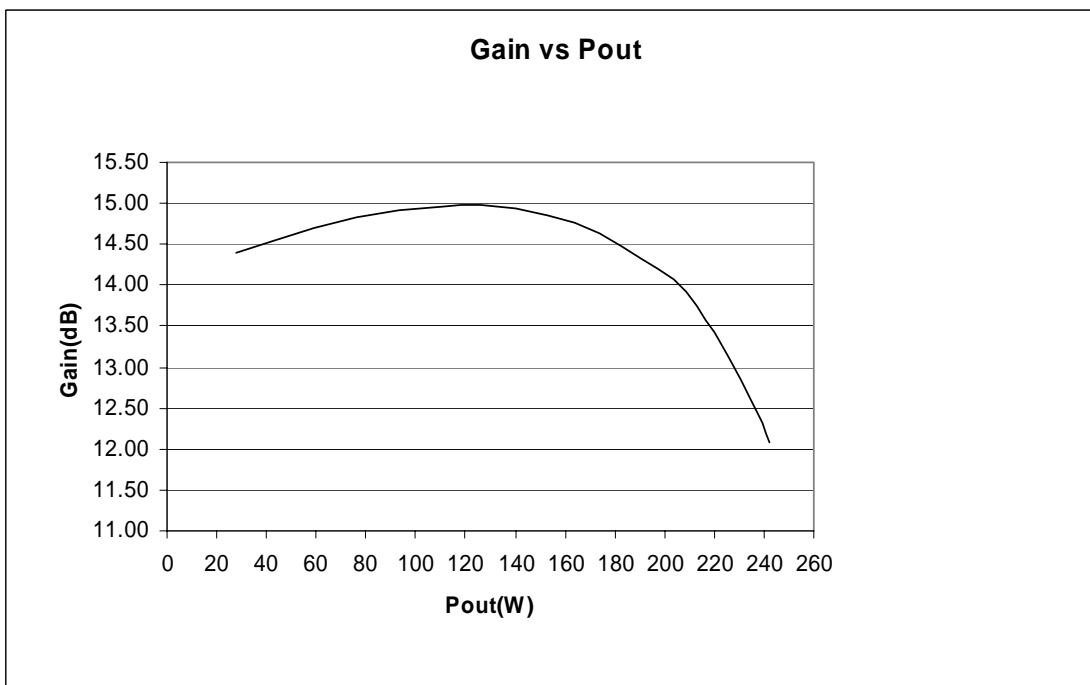
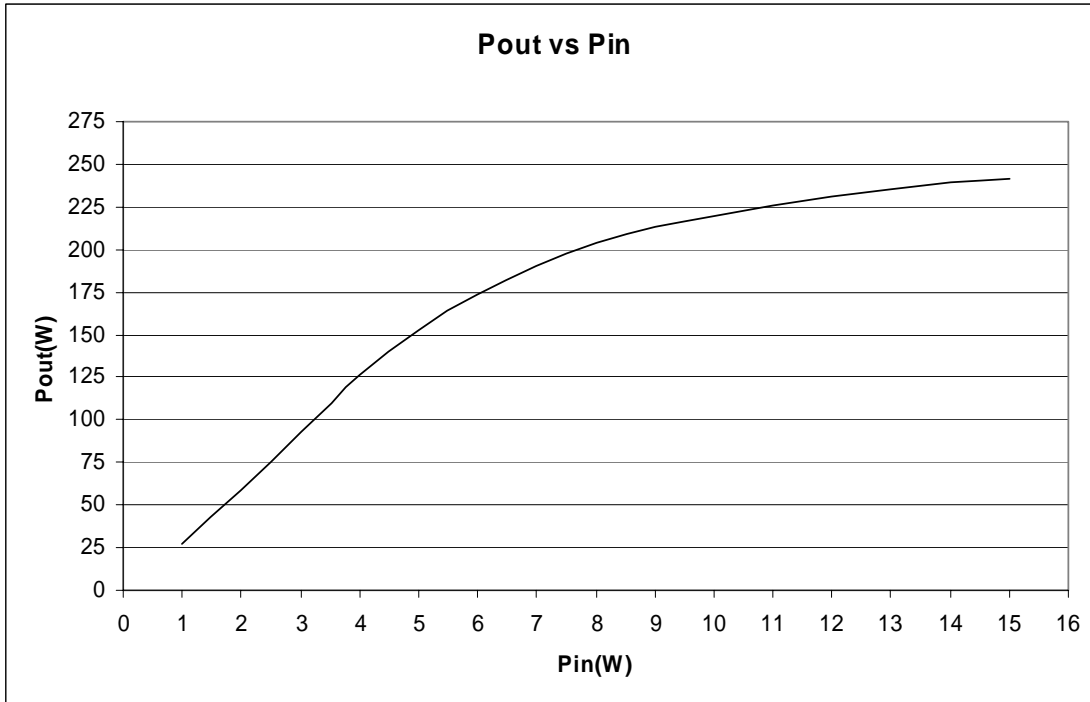
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
$P_{OUT}$	$f = 30 \text{ MHz}$	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 750 \text{ mA}$	220	---	---	WPEP
$G_P$	$f = 30 \text{ MHz}$	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 750 \text{ mA}$	12	---	---	dB
$\eta_C$	$f = 30 \text{ MHz}$	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 750 \text{ mA}$	40	---	---	%
IMD	$f = 30 \text{ MHz}$	$V_{CE} = 28 \text{ V}$	$I_{CQ} = 750 \text{ mA}$	---	---	-30	dBc
$C_{OB}$	$f = 1 \text{ MHz}$	$V_{CB} = 28 \text{ V}$		---	450	---	pf
Conditions	$f1 = 30.000 \text{ MHz}$	$f2 = 30.001 \text{ MHz}$					

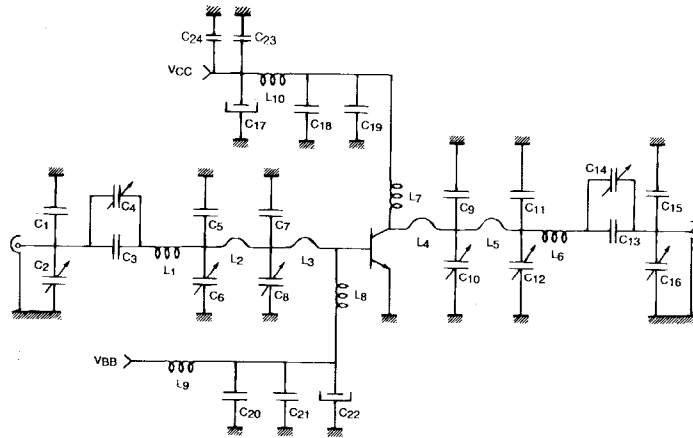
**HFE BINNING (marked on lid with appropriate letter):**

<b>A = 15-19</b>	<b>D = 27-32</b>	<b>G = 45-50</b>
<b>B = 19-22.5</b>	<b>E = 32-38</b>	<b>H = 50-55</b>
<b>C = 22.5-27</b>	<b>F = 38-45</b>	<b>I = 55-60</b>

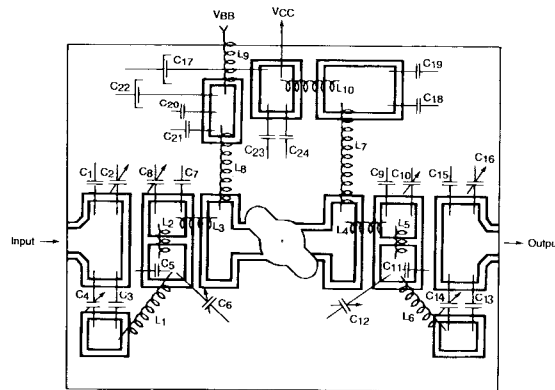
**IMPEDANCE DATA**

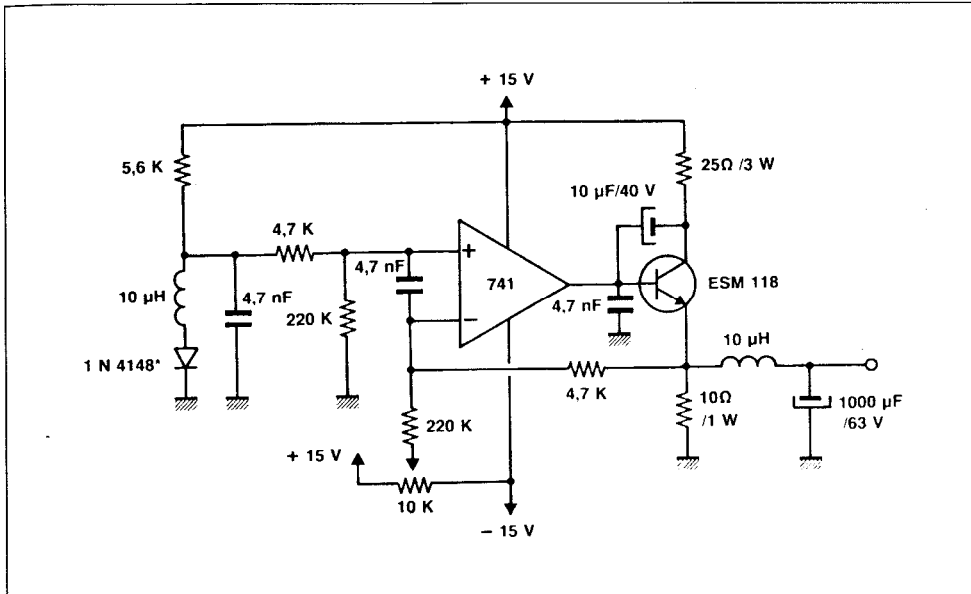
FREQ	$Z_{IN}$	$Z_{CL}$
30 MHz	$1.2 + j0.41$	$1.25 + j1.92$

**TYPICAL PERFORMANCE**

**TEST CIRCUIT**
**TEST CIRCUIT**


- |                          |  |
|--------------------------|--|
| C1 : 180pF               | L1 : 3 Turns, Diameter 10mm, 1.3mm Wire, Length 10mm |
| C2, C4, C6, C8, C10, C12 | L2, L5 : Hair Pin Copper foil 40 x 5mm, 0.2mm Thick  |
| C14, C16 : Arco 428      | L3, L4 : Hair Pin Copper Foil 10 x 5mm, 0.2mm Thick  |
| C3 : 820pF               | L6 : 5 Turns, Diameter 10mm, 1.3mm Wire, Length 15mm |
| C5, C13 : 680pF          | L7 : 3 Turns, Diameter 10mm, 1.3mm Wire, Length 25mm |
| C7, C11 : 1.2nF          | L8 : Choke   |
| C9 : 1.5nF               | L9 : Choke   |
| C17, C22 : 470µF, 40V    | L10 : Choke  |
| C18 : 10nF               |  |
| C19, C21 : 1nF           |  |
| C20, C24 : 100nF, 63V    |  |



**BIASCIRCUIT**

**MS1076**
**PACKAGE MECHANICAL DATA**
